What is claimed is:

1. A liquid crystal display device, comprising:

a first substrate

a main seal on the first substrate and defining a liquid crystal injection area;

a first step coverage-compensating layer disposed between the first substrate and the main seal;

a plurality of dummy seals on the first substrate and external to the liquid crystal injection area; and

a second step coverage-compensating layer disposed between the first substrate and the plurality of dummy seals, the second step coverage-compensating layer having substantially a same thickness as the first step coverage-compensating layer.

2. The liquid crystal display device according to claim 1, wherein the main seal is provided with a liquid crystal injection hole through which a liquid crystal can be injected.

3. The liquid crystal display device according to claim 1, wherein the main seal and the dummy seals have a same thickness.

4. The liquid crystal display device according to claim 1, wherein the first coverage-compensating layer has a thickness of about 6500Å.

5. The liquid crystal display device according to claim 1, wherein a top of the main seal and tops of the dummy seals are a same distance from the first substrate.

6. The liquid crystal display device according to claim 1, further comprising:

a gate metal pattern on the substrate forming a gate line and a gate electrode; and

a gate-insulating layer covering the gate metal pattern.

7. The liquid crystal display device according to claim 6, wherein the first and second step coverage-compensating layers include the gate metal pattern and the gate-insulating layer.

8. The liquid crystal display device according to claim 6, wherein the main seal and the dummy seals are formed on the gate-insulating layer.

9. A method of fabricating a liquid crystal display device, comprising:

forming a first step coverage-compensating layer having a desired thickness on a substrate;

forming a main seal defining a liquid crystal injection area on the first step coverage-compensating layer;

forming a second step coverage-compensating layer on the substrate, wherein the second step coverage-compensating layer has a same thickness as the first step coverage-compensating layer; and

forming a plurality of dummy seals on the second step coverage-compensating layer and external to the main seal.

10. The method according to claim 9, wherein forming the main seal includes forming a liquid crystal injection hole.

11. The method according to claim 9, wherein forming the main seal and forming the dummy seals produce seals having the same height.

12. The method according to claim 9, wherein forming the first coverage-compensating layer and forming the second step coverage-compensating layer produce coverage-compensating layers each having a thickness of about 6500Å.

13. The method according to claim 9, further comprising:

forming a gate metal pattern on the substrate such that the gate metal pattern includes a gate line and a gate electrode;

forming a gate-insulating layer, a semiconductor layer, an ohmic contact layer, and a source/drain metal layer over the gate metal pattern;

patterning the ohmic contact layer and the source/drain metal layer so as to remain on the semiconductor layer but to be removed at positions where the main seal and the dummy seals are to be formed;

forming a passivation layer on the gate-insulating layer in such a manner as to cover the source/drain metal layer;

forming a uniform thickness photo resist on the passivation layer;

patterning the uniform thickness photo resist such that the photo resist on the semiconductor layer has a reduced thickness and such that the photo resist is removed from the positions where the main seal and the dummy seals are to be formed;

patterning the passivation layer and the semiconductor layer by using the photo resist pattern as a mask and such that the passivation layer and the semiconductor layer is removed the positions where the main seal and the dummy seals are to be formed and such that the passivation layer on the semiconductor layer remains and the drain electrode is exposed; and

forming a pixel electrode electrically connected to the drain electrode.

14. The method according to claim 13, wherein each of the first and second step coverage-compensating layers include the gate metal pattern and the gate-insulating layer.

15. The method according to claim 13, wherein the main seal and the dummy seals are formed on the gate-insulating layer.

16. A method of compensating for a cell gap between liquid crystal cells in a liquid crystal display device, comprising:

forming a first step coverage-compensating layer having a desired thickness on a substrate and forming a main seal defining a liquid crystal injection area thereon; and

forming a second step coverage-compensating layer having a same thickness as the first step coverage-compensating layer in such a manner to be arranged outside of the main seal and disposing dummy seals thereon so as to eliminate a step coverage between the main seal and the dummy seals.

17. The method according to claim 16, wherein the first step coverage-compensating layer and the second step coverage-compensating layer are made of same materials and have a same number of stacked-layers.

18. The method according to claim 16, wherein forming the main seal produces a liquid crystal injection hole.

19. The method according to claim 16, wherein the main seal and the dummy seals are formed with a same height.

20. The method according to claim 16, wherein the first and second step coverage-compensating layers are formed at a thickness of about 6500Å.